
2SK2685

GaAs HEMT

HITACHI

ADE-208-400
1st. Edition

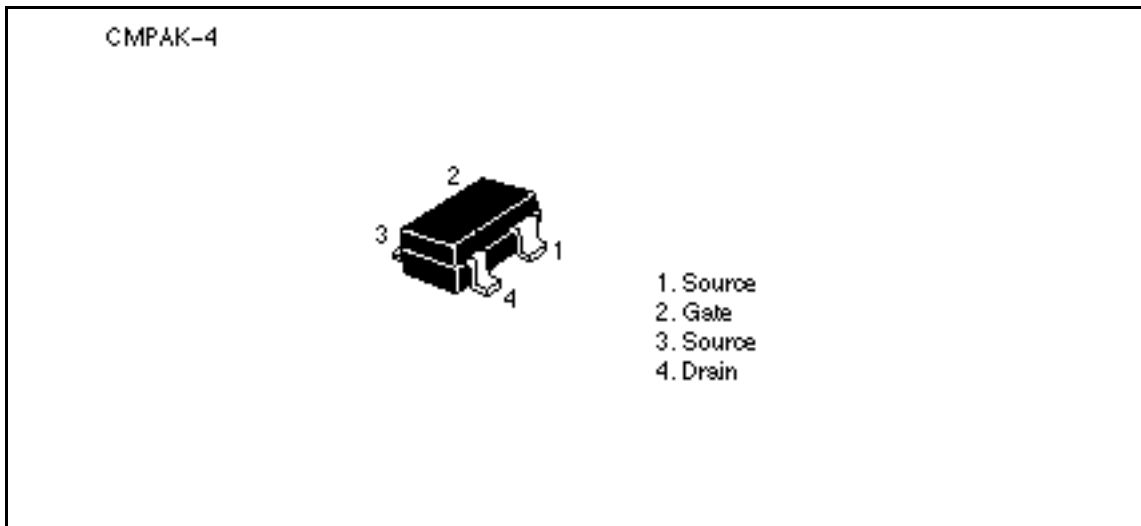
Application

UHF low noise amplifier

Features

- Excellent low noise characteristics.
Fmin = 0.83 dB Typ. (3 V, 10 mA, 2 GHz)
- High associated gain.
Ga = 17 dB Typ. (3 V, 10 mA, 2 GHz)
- High voltage.
 $V_{DS} = 6$ or more voltage.
- Small package. (CMPAK-4)

Outline



2SK2685

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	6	V
Gate to source voltage	V_{GSO}	-6	V
Gate to drain voltage	V_{GDO}	-7	V
Drain current	I_D	20	mA
Channel power dissipation	Pch	100	mW
Channel temperature	Tch	125	°C
Storage temperature	Tstg	-55 to +125	°C

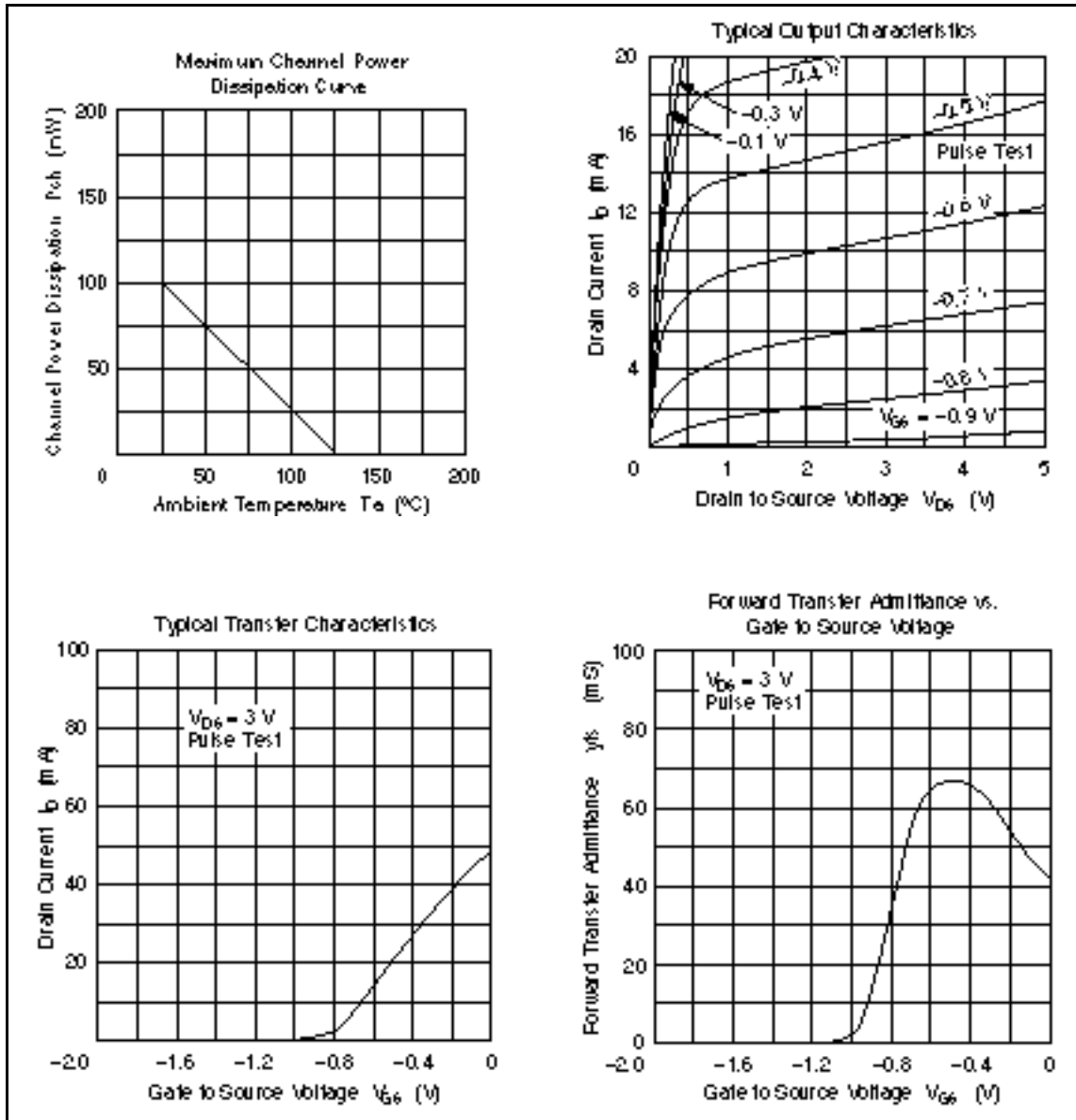
Attention: This device is very sensitive to electro static discharge.

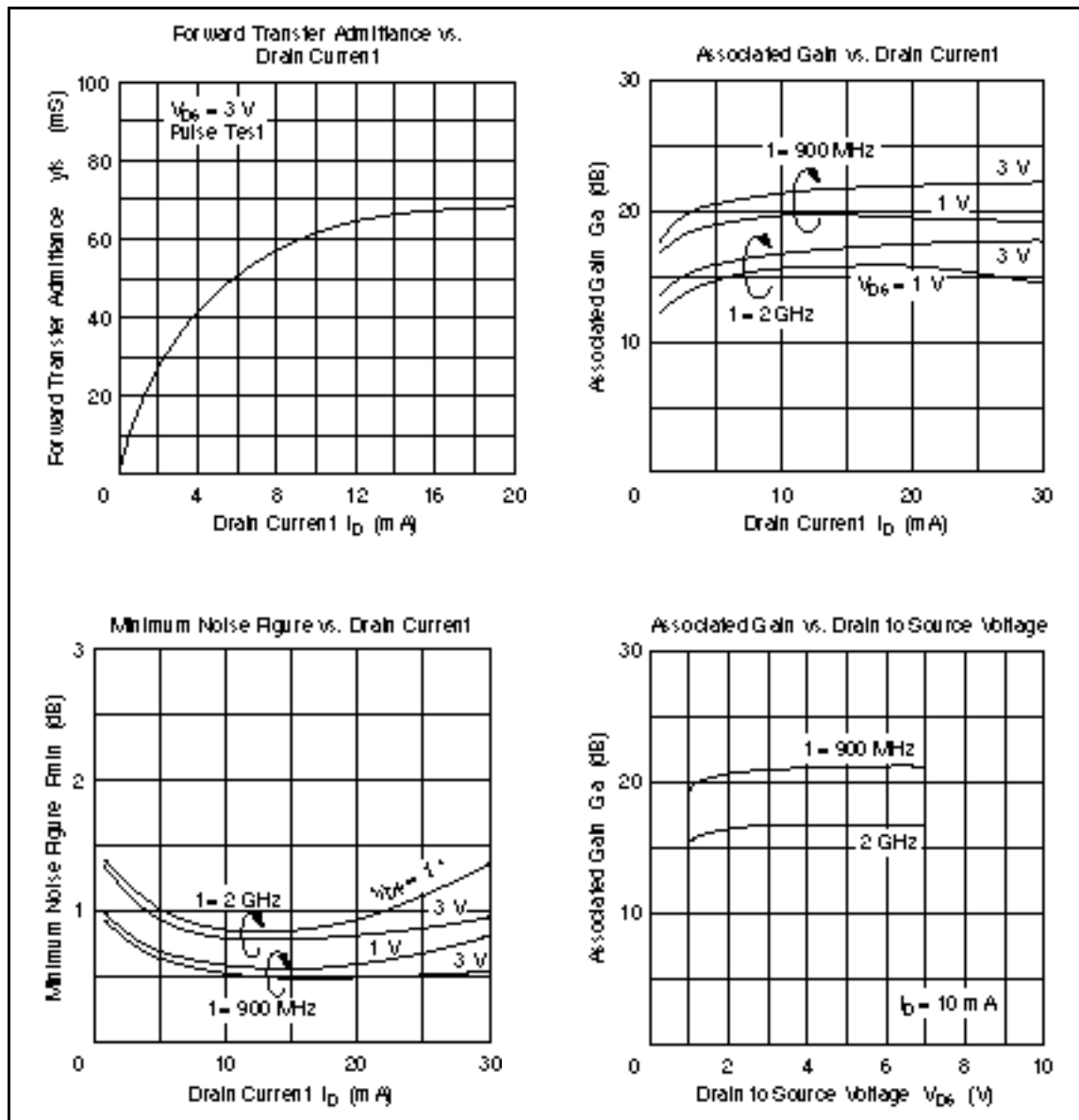
It is recommended to adopt appropriate cautions when handling this transistor.

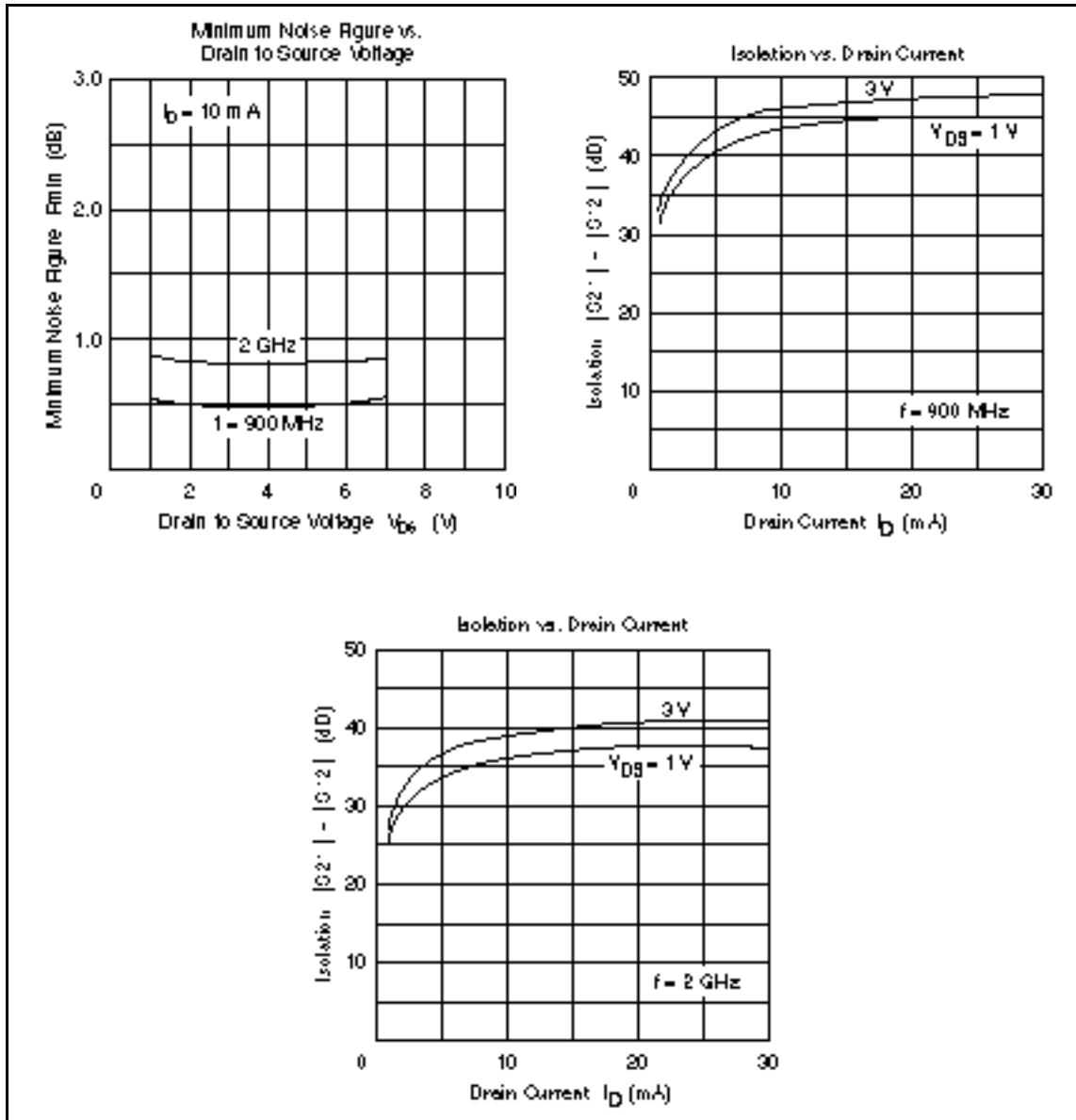
Electrical Characteristics (Ta = 25°C)

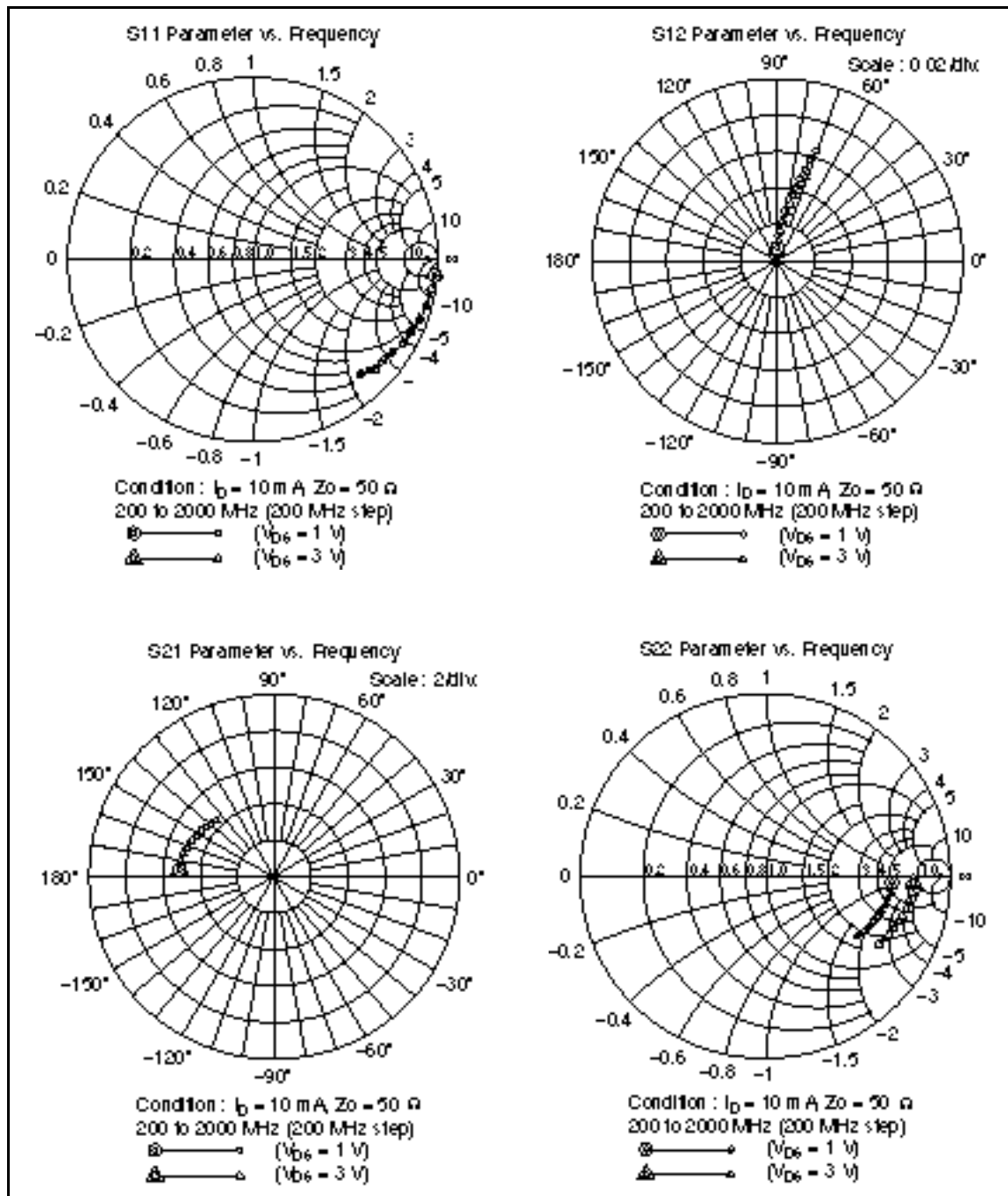
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Gate to source leak current	I_{GSS}	—	—	-20	μ A	$V_{GS} = -6$ V, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.3	—	-2.0	V	$V_{DS} = 3$ V, $I_D = 100$ μ A
Drain current	I_{DSS}	35	50	70	mA	$V_{DS} = 3$ V, $V_{GS} = 0$ (Pulse Test)
Forward transfer admittance	$ y_{fs} $	40	60	—	mS	$V_{DS} = 3$ V, $I_D = 10$ mA, $f = 1$ kHz
Associated gain	Ga	—	17.0	—	dB	$V_{DS} = 3$ V, $I_D = 10$ mA, $f = 2$ GHz
Associated gain	Ga	—	15.2	—	dB	$V_{DS} = 3$ V, $I_D = 3$ mA, $f = 2$ GHz
Associated gain	Ga	16	21.4	—	dB	$V_{DS} = 3$ V, $I_D = 10$ mA, $f = 900$ MHz
Associated gain	Ga	—	19.7	—	dB	$V_{DS} = 3$ V, $I_D = 3$ mA, $f = 900$ MHz
Minimum noise figure	Fmin	—	0.83	—	dB	$V_{DS} = 3$ V, $I_D = 10$ mA, $f = 2$ GHz
Minimum noise figure	Fmin	—	1.08	—	dB	$V_{DS} = 3$ V, $I_D = 3$ mA, $f = 2$ GHz
Minimum noise figure	Fmin	—	0.52	1.0	dB	$V_{DS} = 3$ V, $I_D = 10$ mA, $f = 900$ MHz
Minimum noise figure	Fmin	—	0.74	—	dB	$V_{DS} = 3$ V, $I_D = 3$ mA, $f = 900$ MHz

Note: Marking is "ZT-".









S Parameter ($V_{DS} = 1 \text{ V}$, $I_D = 10 \text{ mA}$, $Z_O = 50 \text{ } \Omega$)

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.996	-4.8	5.12	175.8	0.00691	89.8	0.688	-3.2
400	0.980	-9.5	5.13	169.9	0.0143	88.2	0.682	-6.5
600	0.977	-15.0	5.07	165.4	0.0210	83.3	0.674	-10.6
800	0.970	-19.9	4.94	161.6	0.0276	81.5	0.668	-13.8
1000	0.952	-24.4	4.84	156.5	0.0399	79.3	0.658	-17.2
1200	0.938	-29.2	4.74	152.7	0.0404	76.0	0.648	-20.7
1400	0.916	-34.0	4.67	147.7	0.0462	74.8	0.636	-23.7
1600	0.896	-38.2	4.55	144.1	0.0523	73.1	0.622	-27.1
1800	0.882	-42.9	4.47	140.0	0.0578	72.0	0.611	-29.9
2000	0.859	-47.1	4.36	135.8	0.0630	70.3	0.597	-33.1

S Parameter ($V_{DS} = 3 \text{ V}$, $I_D = 10 \text{ mA}$, $Z_O = 50 \text{ } \Omega$)

Freq. (MHz)	S11		S21		S12		S22	
	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
200	0.998	-4.0	5.13	175.8	0.00581	89.8	0.802	-3.2
400	0.988	-9.2	5.14	170.1	0.0110	85.5	0.796	-6.5
600	0.978	-14.5	5.08	165.2	0.0163	83.3	0.790	-9.8
800	0.968	-19.4	4.95	161.4	0.0216	82.0	0.783	-13.3
1000	0.953	-24.2	4.85	156.4	0.0363	79.2	0.774	-16.4
1200	0.937	-28.7	4.75	152.5	0.0312	76.5	0.764	-19.4
1400	0.917	-33.3	4.68	147.8	0.0358	75.3	0.753	-22.5
1600	0.900	-37.5	4.57	144.0	0.0401	73.2	0.742	-25.4
1800	0.883	-41.9	4.49	140.1	0.0442	72.8	0.731	-28.1
2000	0.858	-46.1	4.37	135.9	0.0477	71.4	0.718	-31.1

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